

Chirality-dependent spin polarization in diffusive metals: linear and quadratic responses

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We study spin polarization induced by electric fields in an isotropic chiral metal with boundaries using the Boltzmann formalism. We calculate both spin polarization in bulk in the linear response and antiparallel spin polarization near the boundary in the quadratic response against electric fields. We also work out spin polarization induced by the fluctuating electric fields, i.e., noises. Based on these results, we address chirality-induced spin selectivity (CISS) without biased inputs, CISS at room temperature, and the enantio-selective interaction between chiral materials and a magnetic substrate.

Introduction.— More than two decades ago, the transmission of electrons through monolayer film of chiral molecules was found to depend on the spin state of the electrons [1]. Ten years later, it was attributed to a spin filter effect of the chiral molecule [2] and was named chirality-induced spin selectivity (CISS) [3–12]. Since then, the CISS has been found in a broader context and the term CISS now describes a general correlation between electron spin polarization and chirality of chiral materials [8–10, 12–15]. The mechanism of CISS is still under debate. However, nonlinear as well as linear response under nonequilibrium state is believed to be essential[11]. Among the phenomena related to CISS, we will focus both on spin polarization in bulk and on antiparallel spin polarization near the surface/interface in chiral metals in the presence of electric fields.

The aim of this letter is two-fold. First, we provide a consistent qualitative understanding of earlier studies on the linear response against the DC driving current [16–20] and those on the quadratic response against the AC driving current [21, 22]. Second, we show that nonequilibrium fluctuation (noise) of electric fields can induce chirality-dependent spin polarization near the surface of chiral metals. This spin polarization is analogous to that in chiral molecules without bias input at room temperature (RT) [23–26], which yields an enantio-specific interaction between chiral molecules and a magnetic substrate with out-of-plane magnetization [23–25, 27]. To address these issues, we consider spin polarization induced by electric fields in the isotropic chiral metal within a scheme of the Boltzmann equation. Throughout this paper, we set $\hbar = 1$ and take $e > 0$.

Model.— We discuss spin dynamics in an isotropic chiral metal, with the simplest model for chiral metals. Here we mean by "chiral" the 3D system with time-reversal symmetry without inversion centers, mirror planes, roto-inversion axes, or roto-reflection axes [28–31]. The Hamiltonian is given by

$$\mathcal{H} = \frac{k^2}{2m} + \alpha \boldsymbol{\sigma} \cdot \mathbf{k}, \quad (1)$$

with $k = |\mathbf{k}|$ and a coupling constant α of the hedgehog type antisymmetric spin-orbit interaction. The energy dispersion relation of the spin-splitting band is given by $\varepsilon_{\pm}(k) = \frac{k^2}{2m} \pm |\alpha|k$. The expectation value of the Pauli matrices for each band is given by $\langle \mathbf{k}, \pm | \boldsymbol{\sigma} | \mathbf{k}, \pm \rangle = \pm \text{sgn}(\alpha) \mathbf{k}/k$. Note that the spin and wave vector are parallel (antiparallel) with each other in the + band when $\alpha > 0$ ($\alpha < 0$). The Fermi wave vectors for the spin-splitting band for the chemical potential $\mu (> 0)$ are given by

$$k_{F,\pm} = m(\mp|\alpha| + v_F), \quad v_F = \sqrt{\alpha^2 + 2\mu/m}. \quad (2)$$

The Boltzmann equation with the relaxation time approximation is given by

$$\frac{\partial f_{\mathbf{k}\gamma}}{\partial t} + \mathbf{v}_{\mathbf{k}\gamma} \cdot \frac{\partial f_{\mathbf{k}\gamma}}{\partial \mathbf{r}} - e \mathbf{E} \cdot \frac{\partial f_{\mathbf{k}\gamma}}{\partial \mathbf{k}} = -\frac{f_{\mathbf{k}\gamma} - f_{\mathbf{k}\gamma}^{(0)}}{\tau} \quad (3)$$

for each subband $\gamma = \pm$. Here $f_{\mathbf{k}\gamma}^{(0)}$ denotes the equilibrium distribution function.

In the following, we define the i th order ($i = 1, 2$) spin density (spin polarization) and the spin current density,

respectively, by

$$s_z^{(i)}(z, t) = \sum_{\gamma=\pm} \int \frac{d\mathbf{k}}{(2\pi)^3} \frac{\langle \mathbf{k}, \gamma | \sigma_z | \mathbf{k}, \gamma \rangle}{2} f_{\mathbf{k}\gamma}^{(i)}(z, t) \quad (4a)$$

$$j_{s;zz}^{(i)}(z, t) = \sum_{\gamma=\pm} \int \frac{d\mathbf{k}}{(2\pi)^3} \langle \mathbf{k}, \gamma | \frac{1}{2} \left\{ \frac{\sigma_z}{2}, \frac{\partial \mathcal{H}}{\partial k_z} \right\} | \mathbf{k}, \gamma \rangle f_{\mathbf{k}\gamma}^{(i)}(z, t). \quad (4b)$$

Here $f_{\mathbf{k}\gamma}^{(i)}(z, t)$ denotes the distribution function of the order of E^i .

Prerequisite: Bulk responses against the uniform electric field.— We first consider the linear and quadratic responses without boundaries as a prerequisite to addressing the effect of boundaries or local input discussed below. By applying the uniform electric field $\mathbf{E} = E_0 \mathbf{e}_z \cos \omega t$, with the unit vector \mathbf{e}_z along the z -axis, we obtain

$$s_z^{(1)}(z, t) = \frac{1}{3} \frac{eE_0\tau}{\pi^2} m^2 \alpha v_F \cos \omega t, \quad j_{s;zz}^{(1)}(z, t) = 0 \quad (5a)$$

$$s_z^{(2)}(z, t) = 0, \quad j_{s;zz}^{(2)}(z, t) = -\frac{7}{15} \frac{(eE_0\tau)^2}{\pi^2} m \alpha v_F \cos^2 \omega t, \quad (5b)$$

when $\omega\tau \ll 1$ by a calculation similar to that in [32]. Spin density then follows dynamics of input charge current density without delay, and thus we can omit the time derivative of spin density in Eq. (3). Figure 1 qualitatively accounts for the linear and quadratic responses shown in Eqs. (5a) and (5b). In the linear response, the nonequilibrium part of the distribution function is anti-symmetric with respect to k_z as shown in Figure 1(a), from which nonzero spin polarization without the spin current in Eq. (5a) follows. On the contrary, in the quadratic response, the nonequilibrium part of the distribution function is symmetric with respect to k_z , (Figure 1(b)), which yields the spin current without spin polarization.

Spin polarization shown in Eq. (5a) is referred to as current-induced magnetization or inverse spin-galvanic effect [33–43]. Expressions for spin current in the quadratic response in different chiral models and related models have been given in earlier studies [32, 44–47].

Spin distribution under locally uniform electric field.— We consider, in the following, the linear and quadratic responses against a *local* electric field $\mathbf{E} = E_0 \mathbf{e}_z \cos \omega t$ exerting on the interval $z \in [0, L]$. We schematically show the set-up in Fig. 2(a).

We seek the solution to Eq. (3) in the form of expansion with respect to E_0 up to the second order. Substituting the resultant distribution function into Eq. (4a) with $i = 1$, we obtain the expression for the spin polarization of

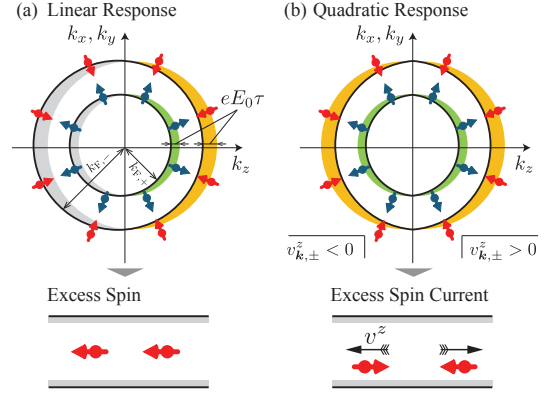


FIG. 1. Schematics for the deviation of the distribution function around the Fermi surfaces of the spin-splitting bands (a) linear and (b) quadratic responses. The shaded regions in oranges or green (gray) denote the excess (deficit) distributions. The arrows represent the direction of spin in each Bloch state. These figures account for the bulk responses shown in Eqs.(5a) and (5b).

the order of E as

$$s_z^{(1)}(z, t) = \frac{eE_0\tau}{2\pi^2} m^2 \alpha v_F \cos \omega t \mathcal{S}^{(1)}(z/\ell, (L-z)/\ell) \quad (6)$$

$$\mathcal{S}^{(1)}(\xi, \xi') := -[\text{sgn}(\xi)F_4(|\xi|) + \text{sgn}(\xi')F_4(|\xi'|)] + \begin{cases} 2/3, & \xi > 0, \xi' > 0 \\ 0, & \text{otherwise} \end{cases} \quad (7)$$

with $\ell = v_F\tau$ and $F_n(\xi) := \int_1^\infty \frac{du}{u^n} \exp(-u\xi)$ for $\xi > 0$. Here, we consider the temperature T much smaller than μ/k_B .

We obtain the spin polarization of the order of E^2 as

$$s_z^{(2)}(z, t) = \frac{(eE_0\tau)^2}{8\pi^2} m \alpha \cos^2 \omega t \left\{ \mathcal{S}^{(2)}(|z/\ell|) - \mathcal{S}^{(2)}(|(L-z)/\ell|) \right\} \quad (8)$$

with

$$\mathcal{S}^{(2)}(\bar{z}) := \bar{z}^2 (F_1(\bar{z}) + F_3(\bar{z})) + 2\bar{z} (F_2(\bar{z}) - F_4(\bar{z})) + 2 (F_3(\bar{z}) - F_5(\bar{z})). \quad (9)$$

The blue (red) curve in Fig. 2 (b) shows the spatial dependence of spin polarization linear (quadratic) to E_0 .

When $\omega = 0$, i.e., the DC electric field, the relative ratio $s_z^{(2)}(z)/s_z^{(1)}(z) \sim eE_0\tau/k_F$, which is much smaller than unity for metals. Thus, for sufficiently small driving currents, the spin density has the same sign at every point in the system, as observed in [16, 18, 19].

However, when $\omega \neq 0$, i.e., the AC electric field, we can measure separately each ω component of spin polarization by using a lock-in amplifier. The red line in Fig. 2(b) shows the static component of spin density,

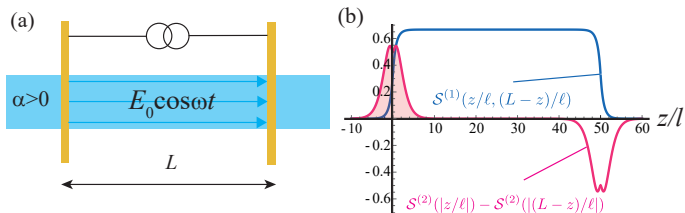


FIG. 2. (a) Schematics for the setup to measure the response against the locally uniform electric field. (b) Spatial dependence of spin polarization in the linear (the blue curve) and quadratic (the red curve) responses against the electric field. Here, we take L to be 50ℓ .

which exhibits antiparallel spin distribution near the interfaces. The static component of spin accumulation areal density, which is half the area of the shaded region in Fig. 2(b), is given by $(1/5\pi^2)(eE_0\tau)^2 m\alpha\ell$. This value accounts for 6/7 (i.e., 85 percent) of that expected from the time averaged spin current $\langle j_{s;zz}^{(2)}(z_{\text{int}}, t) \rangle \simeq -(7/30\pi^2)(eE_0\tau)^2 m\alpha v_F$ (see Eq. (5b)) flowing into the boundary during the time τ . The above comparison implies that antiparallel spin polarization at the boundaries is a consequence of spin current as the quadratic response in bulk together with dissipation near the boundaries. Antiparallel spin distribution near the interface in superconductors with a chiral structure was first observed in [21]. The Boltzmann equation for chiral metals with the relaxation time approximation describes the overall features of spin distribution observed in experiments with both DC[16, 18], and AC [21] driving currents, respectively, as linear and quadratic responses (a remaining issue will be discussed in the Discussion part).

Spin polarization induced by fluctuating electric field.— The spin polarization without biased inputs near the edge or boundary of a chiral molecule has been discussed [8, 23–26]. Further, signals related to spin polarization in chiral metals under bias voltage [16, 18–20] and that in chiral molecules without bias voltage [26] were found to increase around RT. We address these issues on chiral metals.

We have seen that antiparallel spin polarization results from the quadratic response against E , and thus, we expect that a fluctuating E created by nonequilibrium noises suffices to polarize spins near the boundary.

We consider the spin polarization in the 3D isotropic chiral metal induced by a fluctuating electric field

$$E_\mu(t, \mathbf{r}) = \int_{-\infty}^{\infty} \frac{d\omega}{2\pi} E_\mu(\omega, \mathbf{r}) e^{-i\omega t} \quad (10)$$

that satisfies

$$\langle E_\mu(\omega, \mathbf{r}) \rangle = 0, \quad (11a)$$

$$\langle E_\mu(\omega, \mathbf{r}) E_\nu(\omega', \mathbf{r}') \rangle = 2\pi \delta_{\mu\nu} S_E(\omega) \delta(\omega + \omega') g(|\mathbf{r} - \mathbf{r}'|). \quad (11b)$$

We specify the spatial correlation of the fluctuating electric field as

$$g(|\mathbf{r} - \mathbf{r}'|) = \frac{e^{-|\mathbf{r} - \mathbf{r}'|/\lambda_E}}{8\pi\lambda_E^3}, \quad (12)$$

with a correlation length λ_E . We suppose that the chiral metal occupies the region with $z > 0$ and that with $z < 0$ is the vacuum. A set-up is schematically shown in Fig. 3. We assume that the interface $z = 0$ between the chiral metal and the vacuum is not specular but *perfectly rough* for simplicity. The boundary condition on the distribution function $f_{\mathbf{k},\gamma}^{(1,2)}(z)$ is given by (see sec.11.3 in Ziman's monograph [48])

$$f_{\mathbf{k},\gamma}^{(1,2)}(t, \mathbf{r}) = 0, \quad v_{\mathbf{k}\gamma}^z > 0, \quad z = 0 \quad (13a)$$

$$f_{\mathbf{k},\gamma}^{(1,2)}(t, \mathbf{r}) < \infty, \quad v_{\mathbf{k}\gamma}^z < 0, \quad z > 0. \quad (13b)$$

We solve the Boltzmann equation Eq. (3) under the boundary condition Eq. (13) in the presence of electric field Eq. (11) up to the quadratic to E_0 . The expression for the spin polarization $s_z^{(2)}(z)$ after averaging the fluctuating field is available in supplemental material [49].

When the electric field is a white noise, we put $S_E(\omega) = S_E^w$. The expression reduces to

$$s_z^{(2)}(z) = \frac{m\alpha e^2 S_E^w \tau}{32\pi^3 \lambda_E^3} F^w\left(\frac{z}{\ell}\right) \quad (14)$$

with

$$F^w(\xi) := 2\xi \left(e^{-\xi} - \xi \int_\xi^\infty \frac{e^{-t}}{t} dt \right). \quad (15)$$

Figure 3(a) shows the profile of the spin polarization Eq. (14), which is also schematically drawn in Fig. 3(b), where the red arrows represent spin polarization when $\alpha > 0$. Our results also imply the hedge-hog type spin polarization in the sphere of the chiral metals as shown in Fig. 3(c), where the radius of the nano-particle is assumed to be much larger than the mean free path ℓ . In this case, the spin polarization near the surface shown in Fig. 3(c) is locally equivalent to that in Fig. 3(b). By Fig. 3(c), we emphasize that the spin polarization is chirality-dependent (enantio-selective in the terminology of chemistry[31]).

The areal density of the surface spin polarization $s_{\text{surface}}^{(2)} = \int_0^\infty dz s_z^{(2)}(z)$ is given by

$$s_{\text{surface}}^{(2)} = \frac{m\alpha e^2 S_E^w \tau \ell}{48\pi^3 \lambda_E^3}. \quad (16)$$

When $k_B T \ll \mu$, which holds in metals in general at RT, T -dependence of spin polarization is determined by that of S_E^w/λ_E^3 (property of noise/fluctuation) and that of $\tau\ell$ (a property of the chiral metal). As an estimate of the order of the spin polarization in the presence

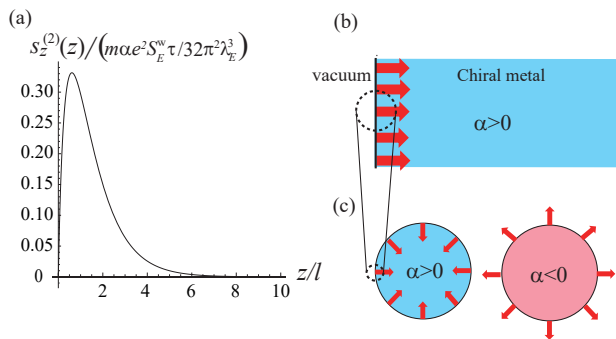


FIG. 3. (a) Spin density induced by the fluctuating electric field in the chiral metal occupying a semi-infinite region with $z > 0$. The boundary $z = 0$ with the vacuum $z < 0$ is perfectly rough. The explicit expression for $s_z^{(2)}$ is given by Eq. (14). m, α, e, τ denote electron mass, the coupling constant of the spin-orbit interaction, and the relaxation time. S_E^w and λ_E , respectively, denote the power spectrum of the white noise of electric fields and the correlation length of the electric fields. (b) Schematics of the spin polarization represented by the red arrows in the chiral metal with $\alpha > 0$. (c) The hedge-hog type spin polarization at the surface of the chiral metal with a spherical shape. When the mean free path ℓ is much smaller than the radius of the sphere, the spin polarization near the surface shown in (c) is locally equivalent to that shown in (b).

of a white noise (14), we assume that the power spectrum has the same form as that for the thermal noise (Johnson-Nyquist noise)[50–52] in the classical regime, $S_E^w \sim k_B T / \sigma_c \sim m k_B T / n_c e^2 \tau$ with the electric conductivity $\sigma_c \sim n_c e^2 \tau / m$ and carrier density n_c of the chiral metal. The expression (16) then reduces to

$$s_{\text{surface}}^{(2)} \sim \frac{m^2 \alpha k_B T \ell}{48 \pi^3 \lambda_E^3 n_c}. \quad (17)$$

When $\lambda_E \sim \ell$, the factor $\frac{k_B T \ell}{\lambda_E^3}$ and thus Eq. (17) increase with increasing temperature.

Discussion.— One caveat is that the Johnson-Nyquist noise of the electric field alone does not induce spin polarization. The latter implies the breaking time-reversal symmetry and it is thus possible only (i) in the presence of the nonequilibrium noise, (ii) equilibrium noise together with another reservoir of a different temperature, or (iii) in a transient state.

Equation (16) and Fig. 3 (c) demonstrate chirality-dependent spin polarization in chiral *metals* induced by fluctuating electric fields.

As an implication to experiments, the radial spin polarization shown in Fig. 3(c) in chiral metals could be used to separate the nanoparticle of chiral metals by a magnetic substrate, similarly to enantio-separation of chiral molecules [24]. The sign of the interaction between the chiral nanoparticle and a substrate magnetized perpendicular to the surface is determined by the spin polarization in the nanoparticle at the point closest to the magnetic substrate and the direction of magnetization

of the substrate. Note that hedge-hog type spin polarization on the spherical chiral nanometals does not change by free rotations. Thus, the interaction between the chiral nanometals and the magnetic substrates remains chirality-dependent.

Let us discuss a possible mechanism of the CISS effect at RT [23–26]. Fransson [53, 54] discussed the spin polarization in chiral molecules at RT by considering the spin-orbit coupling enhanced by the thermal phonon. Contrary to this and other earlier arguments [5, 26, 53–55], however, Eq. (17) suggests that the CISS effect in RT can stem from the fluctuating electric fields that grow with increasing temperature.

Lastly, we remark on an unresolved issue: In Refs. [16–22], spin polarization was observed hundreds of microns or millimeters away from the local input of charge current (, which was dubbed nonlocal effect). The characteristic length scale in our scheme, i.e., 3D isotropic chiral metal with the relaxation time approximation, is the mean free path ℓ , which would be undertaken by the spin diffusion length for more generic models with anisotropic spin-orbit interactions and the anisotropic band structures. The mean free path and the spin-diffusion length are far shorter than the length scale for the experimentally observed nonlocal effect. Thus, the mechanism of the nonlocal effects in chiral metals and superconductors is an open issue that will be explored in future studies.

Summary.— We addressed linear and quadratic responses of spin polarization in 3D isotropic chiral metal against external DC and AC electric fields. We also calculate the surface spin polarization in the chiral metal induced by fluctuating electric fields. We then attribute spin polarization near the surface/interface without bias voltage to quadratic fluctuation or noise of electric fields together with energy dissipation near the surface. We also attribute CISS in RT to T -dependence of the fluctuations of electric fields. Chirality-dependent hedge-hog type spin polarization yields the chirality-specific interaction between a magnetic material and chiral metals subjected to nonequilibrium fluctuation of the electric field.

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Supplemental Materials:

Chirality-dependent spin polarization in diffusive metals: linear and quadratic responses

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S1. DISTRIBUTION FUNCTION OF CHIRAL METALS IN THE PRESENCE OF LOCALLY UNIFORM ELECTRIC FIELD

We consider, in the following, the linear and quadratic responses in the chiral metal Eq. (1) with infinite volume against the locally uniform electric field

$$\mathbf{E} = \begin{cases} E_0 \mathbf{e}_z \cos \omega t, & 0 < z < L \\ 0, & \text{otherwise} \end{cases} \quad (\text{S1})$$

with the use of the Boltzmann equation Eq. (3). We seek the solution to Eq. (3) in the form of expansion with respect to E_0 up to the second order,

$$f_{\mathbf{k}\gamma}(t, z) = f_{\mathbf{k}\gamma}^{(0)} + f_{\mathbf{k}\gamma}^{(1)}(t, z) + f_{\mathbf{k}\gamma}^{(2)}(t, z) + O(E_0^3), \quad (\text{S2})$$

with $f^{(i)}$ being $O(E^i)$. The i -th order distribution function $f_{\mathbf{k}\gamma}^{(i)}$ for $i = 1, 2$ is given, respectively, by

$$f_{\mathbf{k}\gamma}^{(1)} = \text{Re} \left[\tilde{f}_{\omega\mathbf{k}\gamma}^{(1)} e^{-i\omega t} \right],$$

$$f_{\mathbf{k}\gamma}^{(2)} = \frac{1}{2} \text{Re} \left[\tilde{f}_{0,\omega\mathbf{k}\gamma}^{(2)} + \tilde{f}_{2,\omega\mathbf{k}\gamma}^{(2)} e^{-i2\omega t} \right],$$

where $\tilde{f}^{(i)}$ for $i = 1, 2$ satisfies the following equations:

$$\frac{\tilde{f}_{\omega\mathbf{k}\gamma}^{(1)}}{\tau_{1\omega}} + v_{\omega\mathbf{k}\gamma}^{(z)} \frac{\partial \tilde{f}_{\omega\mathbf{k}\gamma}^{(1)}}{\partial z} = \begin{cases} eE_0 \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z}, & 0 < z < L \\ 0, & \text{otherwise,} \end{cases} \quad (\text{S3})$$

$$\frac{\tilde{f}_{n,\omega\mathbf{k}\gamma}^{(2)}}{\tau_{n\omega}} + v_{\mathbf{k}\gamma}^{(z)} \frac{\partial \tilde{f}_{n,\omega\mathbf{k}\gamma}^{(2)}}{\partial z} = \begin{cases} eE_0 \frac{\partial \tilde{f}_{\omega\mathbf{k}\gamma}^{(1)}}{\partial k_z}, & 0 < z < L \\ 0, & \text{otherwise,} \end{cases} \quad (n = 0, 2) \quad (\text{S4})$$

with $1/\tau_{n\omega} = -in\omega + 1/\tau$. We are interested in the case where $\omega\tau \ll 1$ and thus, we replace $\tau_{n\omega}$ by τ and denote $\tilde{f}_{\omega\mathbf{k}\gamma}^{(1)}$ and $\tilde{f}_{n,\omega\mathbf{k}\gamma}^{(2)}$, respectively, by $\tilde{f}_{\mathbf{k}\gamma}^{(1)}$ and $\tilde{f}_{\mathbf{k}\gamma}^{(2)}$. (We note that Eq. (S4) reduces to the same equation.)

First, we consider Eq (S3), which has the solution of the form

$$\tilde{f}_{\mathbf{k}\gamma}^{(1)} \propto \exp \left[-z / (v_{\mathbf{k}\gamma}^{(z)} \tau) \right] \quad (\text{S5})$$

and thus the condition that $\tilde{f}_{\mathbf{k}\gamma}^{(1)}$ is bounded yields

$$\tilde{f}_{\mathbf{k}\gamma}^{(1)}(z) = 0, \quad (\text{S6})$$

for $z < 0$ ($z > L$) when $v_{\mathbf{k}\gamma}^{(z)} > 0$ (< 0). Under this boundary condition (initial condition in the mathematical sense), the solution for $i = 1$ is given by

$$\tilde{f}_{\mathbf{k}\gamma}^{(1)} = -eE_0\tau \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} \begin{cases} 0, & z < 0 \\ \exp \left(-\frac{z}{v_{\mathbf{k}\gamma}^{(z)} \tau} \right) - 1, & 0 < z < L \\ \exp \left(\frac{-z}{v_{\mathbf{k}\gamma}^{(z)} \tau} \right) - \exp \left(\frac{L-z}{v_{\mathbf{k}\gamma}^{(z)} \tau} \right), & L < z \end{cases} \quad (\text{S7})$$

when $v_{\mathbf{k}\gamma}^{(z)} > 0$ and

$$\tilde{f}_{\mathbf{k}\gamma}^{(1)} = -eE_0\tau \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} \begin{cases} \exp\left(\frac{L-z}{v_{\mathbf{k}\gamma}^{(z)}\tau}\right) - \exp\left(\frac{-z}{v_{\mathbf{k}\gamma}^{(z)}\tau}\right), & z < 0 \\ \exp\left(\frac{L-z}{v_{\mathbf{k}\gamma}^{(z)}\tau}\right) - 1, & 0 < z < L \\ 0, & L < z \end{cases} \quad (\text{S8})$$

when $v_{\mathbf{k}\gamma}^{(z)} < 0$. With these inputs (S7) and (S8), the solution to Eq (S4) for $\omega\tau \ll 1$ is given by

$$\tilde{f}_{\mathbf{k}\gamma}^{(2)} = (eE_0\tau)^2 \begin{cases} 0, & z < 0 \\ \left[-\frac{1}{2v_{\mathbf{k}\gamma}^{(z)}} \frac{\partial v_{\mathbf{k}\gamma}^{(z)}}{\partial k_z} \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} \tilde{z}^2 e^{-\tilde{z}} + \frac{\partial^2 f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z^2} (1 - (1 + \tilde{z}) e^{-\tilde{z}}) \right], & 0 < z < L \\ \left[\frac{1}{2v_{\mathbf{k}\gamma}^{(z)}} \frac{\partial v_{\mathbf{k}\gamma}^{(z)}}{\partial k_z} \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} \left((\tilde{L} - \tilde{z})^2 e^{\tilde{L}} - \tilde{z}^2 \right) + \frac{\partial^2 f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z^2} \left(e^{\tilde{L}} (\tilde{z} - \tilde{L}) - \tilde{z} + e^{\tilde{L}} - 1 \right) \right] e^{-\tilde{z}}, & L < z \end{cases} \quad (\text{S9})$$

when $v_{\mathbf{k}\gamma}^{(z)} > 0$ and

$$\tilde{f}_{\mathbf{k}\gamma}^{(2)} = (eE_0\tau)^2 \begin{cases} \left[\frac{1}{2v_{\mathbf{k}\gamma}^{(z)}} \frac{\partial v_{\mathbf{k}\gamma}^{(z)}}{\partial k_z} \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} \left(\tilde{z}^2 - (\tilde{L} - \tilde{z})^2 e^{\tilde{L}} \right) - \frac{\partial^2 f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z^2} \left(e^{\tilde{L}} (\tilde{z} - \tilde{L}) - \tilde{z} + e^{\tilde{L}} - 1 \right) \right] e^{-\tilde{z}}, & z < 0 \\ \left[-\frac{1}{2v_{\mathbf{k}\gamma}^{(z)}} \frac{\partial v_{\mathbf{k}\gamma}^{(z)}}{\partial k_z} \frac{\partial f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z} (\tilde{L} - \tilde{z})^2 e^{\tilde{L}-\tilde{z}} + \frac{\partial^2 f_{\mathbf{k}\gamma}^{(0)}}{\partial k_z^2} \left(1 - e^{\tilde{L}-\tilde{z}} + (\tilde{L} - \tilde{z}) e^{\tilde{L}-\tilde{z}} \right) \right], & 0 < z < L \\ 0, & L < z \end{cases} \quad (\text{S10})$$

when $v_{\mathbf{k}\gamma}^{(z)} < 0$. We have introduced notations $\tilde{z} = z/(v_{\mathbf{k}\gamma}^{(z)}\tau)$ and $\tilde{L} = L/(v_{\mathbf{k}\gamma}^{(z)}\tau)$. Substituting (S7) and (S8) into Eq. (4a) with $i = 1$, we obtain the expression for the spin polarization of the order of E as Eq. (7) in the main text. From Eqs. (S9) and (S10), we can obtain the spin polarization of the order of $O(E^2)$ as Eq. (8) in the main text.

S2. SPIN POLARIZATION INDUCED BY A FLUCTUATING ELECTRIC FIELD NEAR THE SURFACE OF THE CHIRAL METAL

We consider the spin polarization induced by a fluctuating electric field in the 3D isotropic chiral metal near the interface with the vacuum. We suppose that the chiral metal occupies the region with $z > 0$ and that with $z < 0$ is the vacuum. We focus on the case where the interface $z = 0$ between the chiral metal and the vacuum is perfectly rough for simplicity. The boundary condition on the distribution function $f_{\mathbf{k},\gamma}^{(1,2)}(z)$ is given by Eq. (13).

We solve the Boltzmann equation Eq. (3) under the boundary condition (13) in the presence of electric field (11b) up to the quadratic order.

The spin polarization after averaging the fluctuating field is given by

$$s_z^{(2)}(z) = \frac{m\alpha e^2}{16\pi^3 \lambda_E^3} \int \frac{d\omega}{2\pi} S_E(\omega) \left[\frac{(z/v_F) F_2(z/(v_F\tau))}{i\omega + v_F/\lambda_E} + \frac{F_3(z/(1/v_F\tau + 1/\lambda_E + i\omega/v_F)) - F_3(z/v_F\tau)}{(i\omega + v_F/\lambda_E)^2} \right]. \quad (\text{S11})$$

Here F_2 and F_3 have been defined in the main text. When the electric field is a white noise, we put $S_E(\omega) = S_E^\omega$. Equation (S11) reduces to Eq. (14) in the main text.